

Amendments to the Specification

Please replace the title with the following amended title:

DATA REWRITING METHOD FOR FLASH MEMORY USING PARTIAL
ERASES

Please replace the paragraph beginning on page 26, line 17 with the following amended paragraph:

FIG. 13 shows the bit configuration of the memory management area 11a. The two bytes of the memory management area 11a comprise an 8-bit logical sector address area 11b (bits 7 to 0), a 1-bit valid sector flag 11c (bit 8), a 1-bit bad sector flag 11d (bit 9), ~~a 4-bit sector pointer 12e (bits 13 to 10)[[.]]~~ and a 6-bit dummy data area ~~(bits 5 to 10)~~ (bits 15 to 10). The dummy data area is always cleared to "000000".

Please replace the paragraph beginning on page 27, line 1 with the following amended paragraph:

FIG. 14 shows the bit configuration of the buffer data areas 16a. Each of the sixteen 2-byte buffer data areas 16a provided in each buffer sector comprises a 9-bit physical sector address area 16b (bits 8 to 0), a 1-bit write completion flag 16c (bit 9), and a 6-bit dummy data area ~~(bits 5 to 10)~~ (bits 15 to 10). The dummy data is always cleared to "000000".

Please replace the paragraph beginning on page 28, line 32 with the following amended paragraph:

In the rewriting operation in the third embodiment, an application program in the application ROM 3b calls a rewriting subroutine (rewrite control program) from the control ROM 3a, and the control unit 4 controls the operation in accordance with the rewriting subroutine, as in the first embodiment. The rewriting operation in the third embodiment will not be described in further detail.